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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

XF

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	18
Program Memory Size	12KB (12K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 11x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10379ana-w0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.3.2 On-chip oscillator characteristics

(1) High-speed on-chip oscillator oscillation frequency of the R5F102 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip	T _A = -20 to +85 °C	-1.0	+1.0	%
oscillator oscillation	T _A = -40 to -20 °C	-1.5	+1.5	
frequency accuracy	T _A = +85 to +105 °C	-2.0	+2.0	

(2) High-speed on-chip oscillator oscillation frequency of the R5F103 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip	T _A = -40 to + 85 °C	-5.0	+5.0	%
oscillator oscillation				
frequency accuracy				

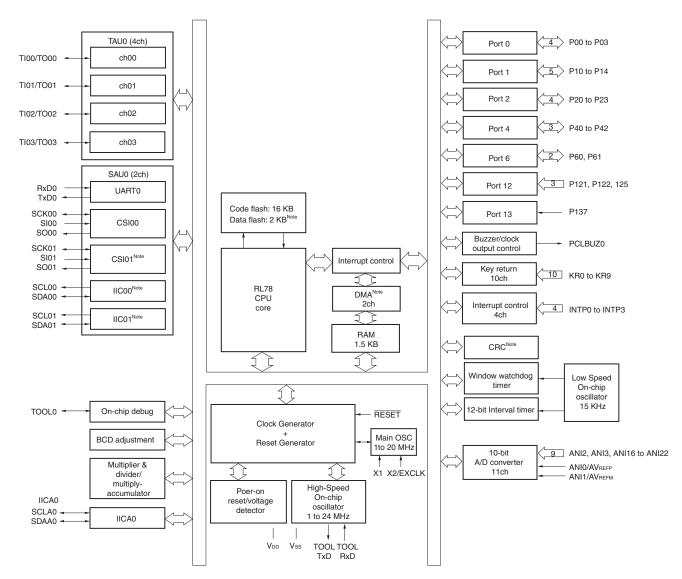
1.3.3 Peripheral Functions

The following are differences in peripheral functions between the R5F102 products and the R5F103 products.

	R5F102	product	R5F103 product			
RL78/G12	20, 24 pin	30 pin product	20, 24 pin	30 pin		
		product		product	product	
Serial interface	UART	1 channel	3 channels	1 channel		
	CSI	2 channels	3 channels	1 channel		
	Simplified I ² C	2 channels	3 channels	None		
DMA function		2 channels		None		
Safety function	CRC operation	Yes		None		
	RAM guard	Yes		None		
	SFR guard	Yes		None		



1.6.2 24-pin products



Note Provided only in the R5F102 products.



<R> 2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +85°C)

<r></r>	This chapter de	scribes the following electrical specifications.
	Target products	A: Consumer applications T _A = -40 to +85°C
<r></r>		R5F102xxAxx, R5F103xxAxx
_		D: Industrial applications $T_A = -40$ to $+85^{\circ}C$
<r></r>		R5F102xxDxx, R5F103xxDxx
		G: Industrial applications when $T_A = -40$ to $+105^{\circ}C$ products is used in the range of $T_A = -40$ to $+85^{\circ}C$
<r></r>		R5F102xxGxx
	Cautions 1.	he RL78 microcontrollers have an on-chip debug function, which is provided for development and

Fautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product.



TA = -40 10 + 00 C,	1.0 V \(\sigma\)	/DD ≤ 5.5 V, Vss = 0 V)			1	1	(2/4
Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Dutput current, low ^{Note 1}	lol1	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				20.0 Note 2	mA
		Per pin for P60, P61				15.0 Note 2	mA
		20-, 24-pin products:	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			60.0	mA
		Total of P40 to P42	$2.7~V \leq V_{\text{DD}} < 4.0~V$			9.0	mA
		30-pin products: Total of P00, P01, P40, P120 (When duty $\leq 70\%^{\text{Note 3}}$)	$1.8~V \leq V_{\text{DD}} < 2.7~V$			1.8	mA
		20-, 24-pin products:	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			80.0	mA
		Total of P00 to P03 ^{Note 4} ,	$2.7~V \leq V_{\text{DD}} < 4.0~V$			27.0	mA
	$ \begin{array}{c} \mbox{P10 to P14, P60, P61} \\ \mbox{30-pin products:} \\ \mbox{Total of P10 to P17, P30, P31, P50,} \\ \mbox{P51, P60, P61, P147} \\ \mbox{(When duty \leq 70\% $^{Note 3}$)} \end{array} $			5.4	mA		
		Total of all pins (When duty $\leq 70\%^{Note 3}$)				140	mA
	IOL2	Per pin for P20 to P23				0.4	mA
		Total of all pins				1.6	mA

(0)

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor \leq 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

• Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and $I_{OL} = 10.0 \text{ mA}$

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \cong 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- 4. 24-pin products only.
- Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(3/4)

Parameter	Symbol	Condition	S	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	Normal input buffer		0.8Vpp		VDD	V
		20-, 24-pin products: P00 to P0 P40 to P42)3 ^{№te 2} , P10 to P14,				
		30-pin products: P00, P01, P1 P40, P50, P51, P120, P147	0 to P17, P30, P31,				
	VIH2	TTL input buffer	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	2.2		Vdd	V
		20-, 24-pin products: P10, P11	$3.3~V \leq V_{\text{DD}} < 4.0~V$	2.0		VDD	V
		30-pin products: P01, P10, P11, P13 to P17	$1.8~V \leq V_{\text{DD}} < 3.3~V$	1.5		VDD	V
	VIH3	P20 to P23		0.7Vdd		VDD	V
	VIH4	P60, P61		0.7Vdd		6.0	V
	VIH5	P121, P122, P125 ^{Note 1} , P137, I	0.8VDD		VDD	V	
Input voltage, low	VIL1	Normal input buffer	0		0.2V _{DD}	V	
		20-, 24-pin products: P00 to P0 P40 to P42					
		30-pin products: P00, P01, P10 P40, P50, P51, P120, P147					
	VIL2	TTL input buffer	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	0		0.8	V
		20-, 24-pin products: P10, P11	$3.3~V \leq V_{\text{DD}} < 4.0~V$	0		0.5	V
		30-pin products: P01, P10, P11, P13 to P17	$1.8~V \leq V_{\text{DD}} < 3.3~V$	0		0.32	V
	VIL3	P20 to P23		0		0.3VDD	V
	VIL4	P60, P61		0		0.3VDD	V
	VIL5	P121, P122, P125 ^{Note 1} , P137, I	EXCLK, RESET	0		0.2VDD	V
Output voltage, high	V _{OH1}	20-, 24-pin products: P00 to P03 ^{№ete 2} , P10 to P14,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -10.0 \ \text{mA} \end{array}$	VDD-1.5			V
		P40 to P42 30-pin products:	4.0 V \leq V_{DD} \leq 5.5 V, I_{OH1} = -3.0 mA	VDD-0.7			V
	P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120,	$\begin{array}{l} 2.7 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}, \\ \text{I}_{\text{OH1}} = -2.0 \ \text{mA} \end{array}$	Vdd-0.6			V	
		P147	$\begin{array}{l} 1.8 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -1.5 \ mA \end{array}$	V _{DD} -0.5			V
	V _{OH2}	P20 to P23	Іон2 = -100 <i>µ</i> А	VDD-0.5			V

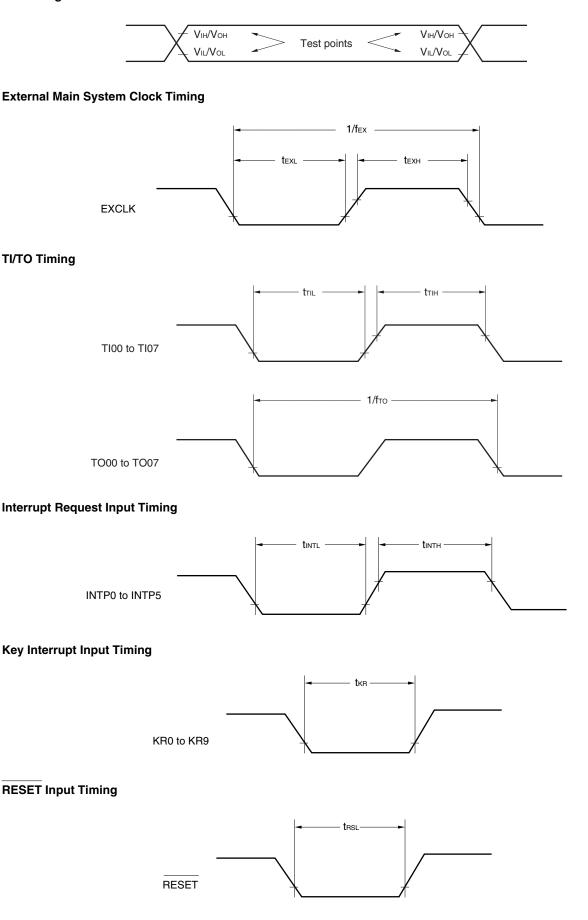
Notes 1. 20, 24-pin products only.

2. 24-pin products only.

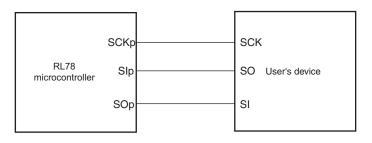
- Caution The maximum value of V_H of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



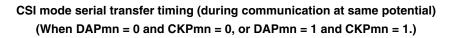
AC Timing Test Point

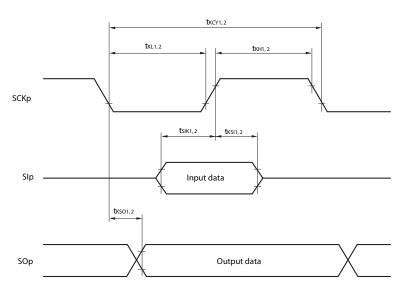




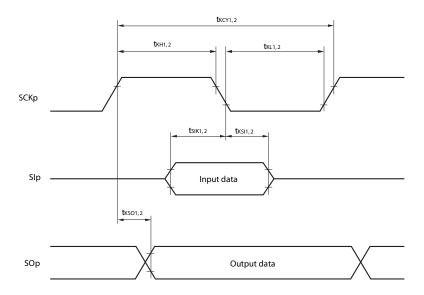


CSI mode connection diagram (during communication at same potential)





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



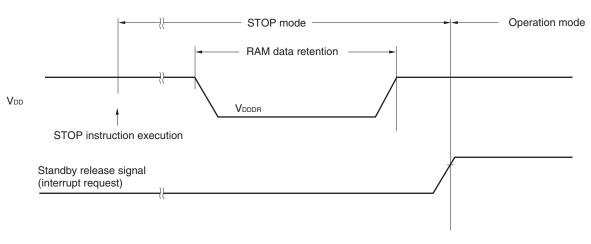
(Remarks are listed on the next page.)



<R> 2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

(T _A = -40 to +85°C, V _{ss} = 0 V)									
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit			
Data retention supply voltage	Vdddr		1.46 ^{Note}		5.5	V			

<R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

<r></r>	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	System clock frequency	fclĸ		1		24	MHz
	Code flash memory rewritable times	Cerwr	Retained for 20 years	1,000			Times
	Notes 1, 2, 3		$T_A = 85^{\circ}C$				
	Data flash memory rewritable times		Retained for 1 year		1,000,000		
	Notes 1, 2, 3		$T_A = 25^{\circ}C$				
			Retained for 5 years	100,000			
			$T_A = 85^{\circ}C$				
			Retained for 20 years	10,000			
			$T_A = 85^{\circ}C$				

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.



2.9 Dedicated Flash Memory Programmer Communication (UART)

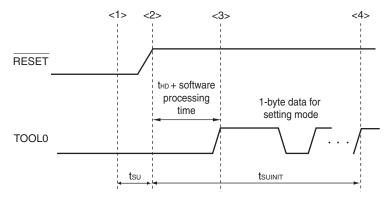
Parameter	Symbol	nbol Conditions		TYP.	MAX.	Unit			
Transfer rate		During serial programming	115,200		1,000,000	bps			

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

2.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset are released before external reset release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	ts∪	POR and LVD reset are released before external reset release	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset are released before external reset release	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level
 - the: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



<R> 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

<R> This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$

<R> R5F102xxGxx

- **Cautions 1.** The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product.
 - **3.** Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to $+105^{\circ}C$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When the RL78 microcontroller is used in the range of T_A = -40 to +85 °C, see CHAPTER 28 <R> ELECTRICAL SPECIFICATIONS (A: T_A = -40 to +85 °C).

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}C$)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Арр	lication
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode	HS (high-speed main) mode:	HS (high-speed main) mode only:
Operating voltage range	$2.7~V \leq V_{\text{DD}} \leq 5.5~V@1~MHz$ to 24 MHz	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$ @ 1 MHz to 24 MHz
	$2.4~V \leq V_{\text{DD}} \leq 5.5~V@1~\text{MHz}$ to 16 MHz	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$ @1 MHz to 16 MHz
	LS (low-speed main) mode:	
	1.8 V \leq V_{DD} \leq 5.5 V@1 MHz to 8 MHz	
High-speed on-chip oscillator clock	R5F102 products, 1.8 V \leq V_DD \leq 5.5 V:	R5F102 products, 2.4 V \leq V _{DD} \leq 5.5 V:
accuracy	±1.0%@ T _A = -20 to +85°C	±2.0%@ T _A = +85 to +105°C
	$\pm 1.5\%$ @ T _A = -40 to -20°C	±1.0%@ T _A = -20 to +85°C
	R5F103 products, 1.8 V \leq V_DD \leq 5.5 V:	±1.5% @ T _A = -40 to -20°C
	±5.0%@ T _A = -40 to +85°C	
Serial array unit	UART	UART
	CSI: fcLK/2 (supporting 12 Mbps), fcLK/4	CSI: fclk/4
	Simplified I ² C communication	Simplified I ² C communication
Voltage detector	Rise detection voltage: 1.88 V to 4.06 V	Rise detection voltage: 2.61 V to 4.06 V
	(12 levels)	(8 levels)
	Fall detection voltage: 1.84 V to 3.98 V	Fall detection voltage: 2.55 V to 3.98 V
	(12 levels)	(8 levels)

Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to 29.1 to 29.10.



(2) 30-pin products

(T _A = -40 to	$(T_{A} = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}) $ (1/2)									(1/2)
Parameter	Symbol		Conditions					TYP.	MAX.	Unit
Supply		Operating	HS (High-speed	$f_{\text{IH}} = 24 \; MHz^{\text{Note 3}}$	Basic	VDD = 5.0 V		1.5		mA
current ^{Note 1}		mode	main) mode ^{№084}		operation	VDD = 3.0 V		1.5		
					Normal	V _{DD} = 5.0 V		3.7	5.8	mA
					operation	VDD = 3.0 V		3.7	5.8	
				f⊮ = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.7	4.2	mA
						VDD = 3.0 V		2.7	4.2	
				$f_{MX} = 20 \text{ MHz}^{Note 2},$		Square wave input		3.0	4.9	mA
				$V_{\text{DD}} = 5.0 \text{ V}$		Resonator connection		3.2	5.0	
				$f_{MX}=20\ MHz^{\text{Note 2}},$		Square wave input		3.0	4.9	mA
				$V_{\text{DD}} = 3.0 \text{ V}$		Resonator connection		3.2	5.0	
				$f_{MX} = 10 \text{ MHz}^{Note 2},$		Square wave input		1.9	2.9	mA
				$V_{\text{DD}} = 5.0 \text{ V}$		Resonator connection		1.9	2.9	
				$f_{MX} = 10 \text{ MHz}^{Note 2},$		Square wave input		1.9	2.9	mA
				$V_{\text{DD}} = 3.0 \text{ V}$		Resonator connection		1.9	2.9	

Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

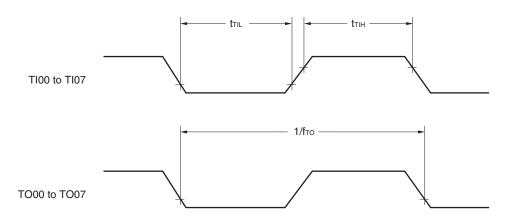
- 2. When high-speed on-chip oscillator clock is stopped.
- 3. When high-speed system clock is stopped
- 4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: VDD = 2.7 V to 5.5 V @1 MHz to 24 MHz VDD = 2.4 V to 5.5 V @1 MHz to 16 MHz

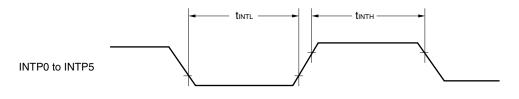
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



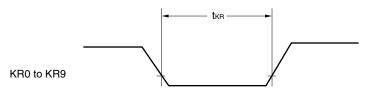
TI/TO Timing



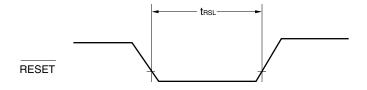
Interrupt Request Input Timing



Key Interrupt Input Timing



RESET Input Timing





Parameter	Symbol	Conditions		HS (high-spee	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tKCY1	$t_{\text{KCY1}} \geq 4/f_{\text{CLK}}$	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	334		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	500		ns
SCKp high-/low-level width	tкнı,			tксү1/2–24		ns
	tĸ∟ı			tксү1/2–36		ns
				tксү1/2–76		ns
SIp setup time (to SCKp \uparrow) ^{Note 1}	tsik1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$		66		ns
		$2.7~V \le V_{\text{DD}} \le 5.$	5 V	66		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		113		ns
SIp hold time (from SCKp \uparrow) Note 2	tksi1			38		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	$C = 30 \text{ pF}^{Note4}$			50	ns

(2) During communication at same potential (CSI mode) (master mode, SCKp internal clock output)
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.
- **Caution** Select the normal input buffer for the SIp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).
- **Remarks 1.** p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)
 - 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3))



Baud rate error (theoretical value) =

$$) = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \,[\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =

 $\begin{array}{c} \displaystyle \frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \\ \hline \\ \displaystyle (\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits} \end{array} \times 100 \ [\%]$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 6. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.
- 7. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq V_DD < 3.3 V, 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =

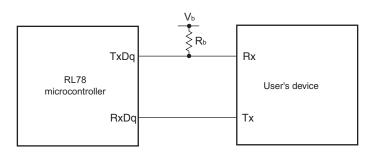
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \,[\%]$

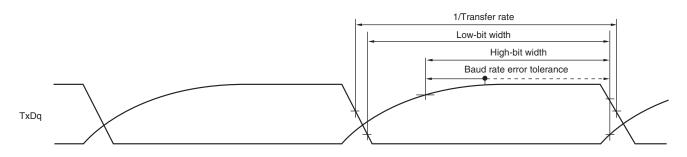
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 7 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

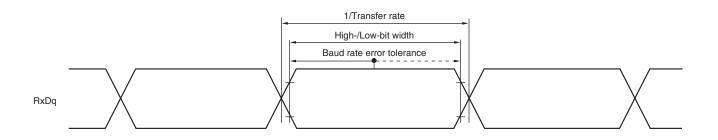


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 - fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

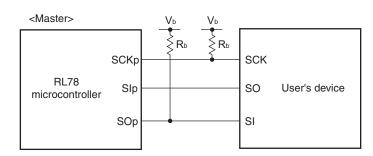
Parameter	Symbol	Conditions	HS (high-speed	main) Mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) _{Note}	tsik1	$ \begin{array}{l} \label{eq:VDD} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{b} \leq 4.0 \ V, \\ C_{b} = 30 \ pF, \ R_{b} = 1.4 \ k\Omega \end{array} $	88		ns
		$\label{eq:VD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} < 4.0 \ V, \ 2.3 \ V \leq V_{b} \leq 2.7 \ V, \\ C_{b} = 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$	88		ns
		$\label{eq:VD} \begin{array}{l} 2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{b} \leq 2.0 \ V, \\ C_{b} = 30 \ pF, \ R_{b} = 5.5 \ k\Omega \end{array}$	220		ns
Slp hold time (from SCKp↓) ^{№te}	tksii		38		ns
		$\label{eq:VD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} < 4.0 \ V, \ 2.3 \ V \leq V_{b} \leq 2.7 \ V, \\ C_{b} = 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$	38		ns
		$\label{eq:VD} \begin{array}{l} 2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V, \\ C_{\text{b}} = 30 \ p\text{F}, \ R_{\text{b}} = 5.5 \ k\Omega \end{array}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1			50	ns
		$\label{eq:VD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} < 4.0 \ V, \ 2.3 \ V \leq V_{b} \leq 2.7 \ V, \\ C_{b} = 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$		50	ns
		$\label{eq:VD} \begin{array}{l} 2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V, \\ C_{\text{b}} = 30 \ p\text{F}, \ R_{\text{b}} = 5.5 \ k\Omega \end{array}$		50	ns

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

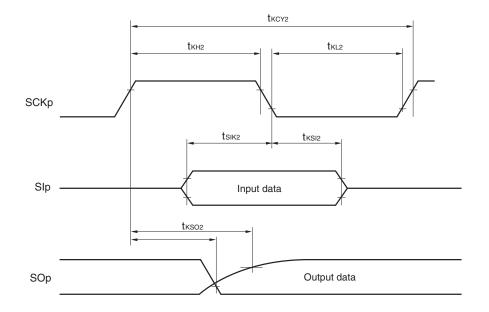
Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.
- **Remarks 1.** R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

CSI mode connection diagram (during communication at different potential)







CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)



3.5.2 Serial interface IICA

Parameter	Symbol	Conditions	HS	HS (high-speed main) mode			Unit
			Standa	rd Mode	Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Fast mode: fclk≥ 3.5 MHz			0	400	kHz
		Normal mode: fcLK≥ 1 MHz	0	100			kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	t∟ow		4.7		1.3		μS
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	t BUF		4.7		1.3		μS

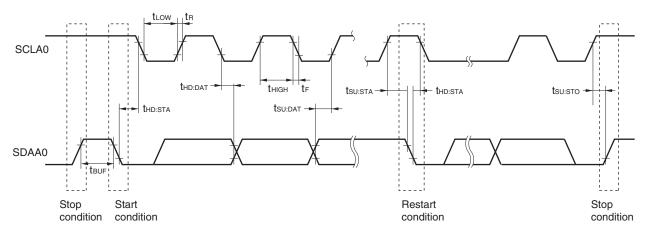
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- **Caution** Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

 $\label{eq:cb} \begin{array}{ll} \mbox{Normal mode:} & C_b = 400 \mbox{ pF}, \mbox{ Rb} = 2.7 \mbox{ } k\Omega \\ \mbox{Fast mode:} & C_b = 320 \mbox{ pF}, \mbox{ Rb} = 1.1 \mbox{ } k\Omega \end{array}$



IICA serial transfer timing



<R>

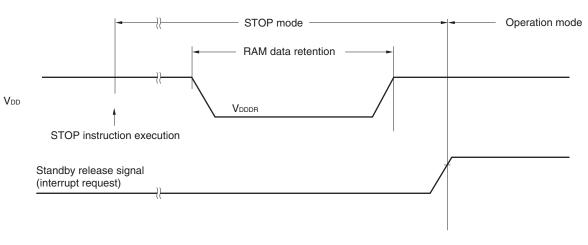
<R>

<R> 3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	Vdddr		1.44 ^{Note}		5.5	V

<R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclк		1		24	MHz
Code flash memory rewritable times Notes 1, 2, 3	Cerwr	Retained for 20 years $T_A = 85^{\circ}C^{Notes 4}$	1,000			Times
Data flash memory rewritable times Notes 1, 2, 3		Retained for 1 year T _A = $25^{\circ}C^{Notes 4}$		1,000,000		
		Retained for 5 years $T_A = 85^{\circ}C^{Notes 4}$	100,000			
		Retained for 20 years T _A = $85^{\circ}C^{Notes 4}$	10,000			

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- 4. This temperature is the average value at which data are retained.



			Description
Rev.	Date	Page	Summary
2.00	Sep 06, 2013	55	Modification of description and Notes 3 and 4 in 2.6.1 (3)
		56	Modification of description and Notes 3 and 4 in 2.6.1 (4)
		57	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		57	Modification of table and Note in 2.6.3 POR circuit characteristics
		58	Modification of table in 2.6.4 LVD circuit characteristics
		59	Modification of table of LVD detection voltage of interrupt & reset mode
		59	Modification of number and title to 2.6.5 Power supply voltage rising slope characteristics
		61	Modification of table, figure, and Remark in 2.10 Timing of Entry to Flash Memory
			Programming Modes
		62 to 103	Addition of products of industrial applications (G: $T_A = -40$ to $+105^{\circ}C$)
		104 to 106	Addition of products of industrial applications (G: $T_A = -40$ to $+105^{\circ}C$)
2.10	2.10 Mar 25, 2016	6	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G12
		7	Modification of Table 1-1 List of Ordering Part Numbers
		8	Addition of product name (RL78/G12) and description (Top View) in 1.4.1 20-pin products
		9	Addition of product name (RL78/G12) and description (Top View) in 1.4.2 24-pin products
		10	Addition of product name (RL78/G12) and description (Top View) in 1.4.3 30-pin products
		15	Modification of description in 1.7 Outline of Functions
		16	Modification of description, and addition of target products
		52	Modification of note 2 in 2.5.2 Serial interface IICA
		60	Modification of title and note, and addition of caution in 2.7 RAM Data Retention Characteristics
		60	Modification of conditions in 2.8 Flash Memory Programming Characteristics
		62	Modification of description, and addition of target products and remark
		94	Modification of note 2 in 3.5.2 Serial interface IICA
		102	Modification of title and note in 3.7 RAM Data Retention Characteristics
		102	Modification of conditions in 3.8 Flash Memory Programming Characteristics
		104 to 106	Addition of package name

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